

isc N-Channel Mosfet Transistor

BUZ93

FEATURES

- High speed switching
- Low R_{DS(ON)}
- · Easy driver for cost effective application
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

- Automotive power actuator drivers
- Motor controls
- DC-DC converters

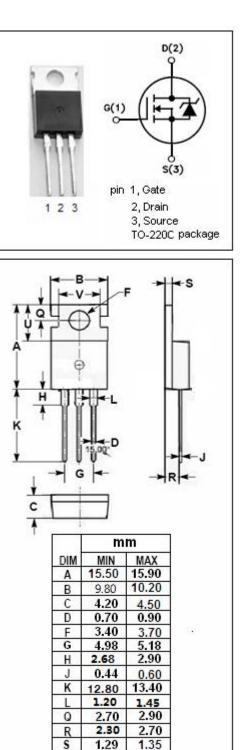
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | ARAMETER | VALUE | UNIT | | |
|------------------|---|---------|------|--|--|
| V _{DSS} | Drain-Source Voltage (V _{GS} =0) | 600 | V | | |
| V _{GS} | Gate-Source Voltage | ±20 | V | | |
| ID | Drain Current-continuous@ TC=25℃ | 3.6 | А | | |
| I _{DM} | Drain Current-Single Plused | 14.5 | А | | |
| P _{tot} | Total Dissipation@TC=25°C | 80 | W | | |
| Tj | Max. Operating Junction Temperature | 150 | °C | | |
| T _{stg} | Storage Temperature Range | -55~150 | °C | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|---------------------|---|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 1.56 | °C/W |
| R _{th j-a} | Thermal Resistance, Junction to Ambient | 75 | °C/W |

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYPE | МАХ | UNIT |
|---------------------|---------------------------------|---|-----|------|------|------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D =0.25mA | 600 | | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} = V _{GS} ; I _D =1mA | 2.1 | | 4.0 | V |
| V_{SD} | Diode Forward On-voltage | I _S = 6.6A ;V _{GS} = 0 | | | 1.4 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 2A | | | 2.5 | Ω |
| Igss | Gate-Body Leakage Current | V _{GS} = ±20V;V _{DS} = 0 | | | ±100 | nA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =600V; V _{GS} = 0 | | | 1 | μA |
| Gfs | Forward Transconductance | V _{DS} = 25V; I _D =2A | 2.1 | | | S |
| t _{d(on)} | Turn-on Delay Time | V _{GS} =10V; | | | 15 | |
| tr | Rise Time | I _D =2.3A; | | | 70 | |
| $t_{\rm d(off)}$ | Turn-off Delay Time | V _{DD} =30V; R _{GS} =50 Ω | | | 95 | ns |
| tr | Fall Time | | | | 55 | |

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